

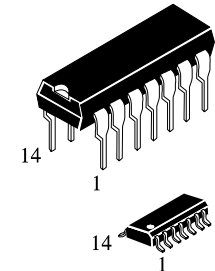
Quad 2-Input NOR Gate

IN74LV02

The IN74LV02 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT02A, 74ALS02

Features:

- Wide Operating Voltage: 1.0~5.5 V
- Input voltage levels are compatible with standard C-MOS levels
- Accepts TTL input levels between $V_{CC} = 2.7 V$ and $V_{CC} = 3.6 V$
- Output voltage levels are compatible with input levels C-MOS, N-MOS and TTL microcircuits.
- Maximum input current : 1.0 mA
- Consumption current : 8 mA.



N SUFFIX PLASTIC

D SUFFIX SOIC

ORDERING INFORMATION

IN74LV02N DIP
IN74LV02D SOIC

$T_A = -40^\circ$ to $125^\circ C$ for all packages

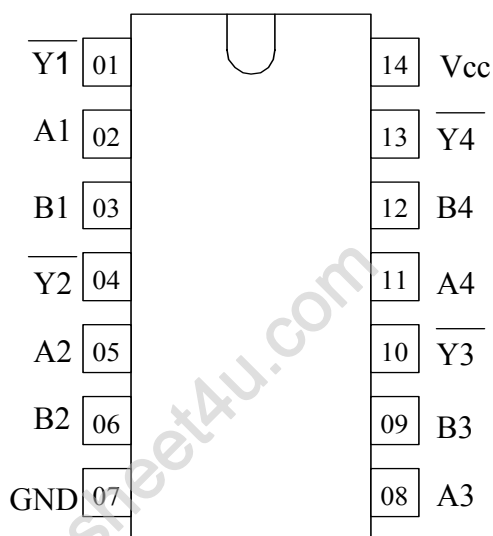
IN74LV02 truth table

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Input		Output
A	B	$Y = \overline{A + B}$
L	L	H
L	H	L
H	L	L
H	H	L

**Note – H - high voltage level;
L - low voltage level;**

Pinout



Pins description in IN74LV02

Pin No.	Symbol	Pin description
01	$\overline{Y1}$	Output
02	A1	Input
03	B1	Input
04	$\overline{Y2}$	Output
05	A2	Input
06	B2	Input
07	GND	Common output
08	A3	Input
09	B3	Input
10	$\overline{Y3}$	Output
11	A4	Input
12	B4	Input
13	$\overline{Y4}$	Output
14	V_{CC}	Supply output from voltage source

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	-0.5 ~ +5.5	V
I_{IK}^{*1}	Input diode current	±20	mA
I_{OK}^{*2}	Output diode current	±50	mA
I_O^{*3}	Output current source-drain	±25	mA
I_{CC}	Supply output current	±50	mA
I_{GND}	Common output current	±50	mA
P_D	Dissipation power at free air change, Plastic DIP SOIC ^{*4}	750 500	mW
Tstg	Storage temperature	-65 ~ +150	°C
T_L		260	°C

* Under absolute maximum conditions operation of microcircuits is not guaranteed. Operation under maximum conditions is guaranteed.

*¹ If $V_I < -0.5V$ or $V_I > V_{CC} + 0.5 V$.

*² If $V_O < -0.5V$ or $V_O > V_{CC} + 0.5 V$.

*³ If $-0.5V < V_O < V_{CC} + 0.5 V$.

*⁴ Under operation in the temperature range from 65°C to 125°C value of dissipation power drops down - to 12 mW/°C for Plastic DIP
- to 8 mW/°C for SOIC

Maximum conditions

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage	1.2	5.5	V
V_{IN}	Input voltage	0	V_{CC}	V
V_{OUT}	Output voltage	0	V_{CC}	V
T_A	Operation temperature. For all packages	-40	125	°C
t_{LH}, t_{HL}	Period of signal rise and fall edges (Figure 1)	$1.0 \leq V_{CC} < 1.2 B$ $2.0 \leq V_{CC} < 2.7 B$ $2.7 \leq V_{CC} < 3.6 B$ $3.6 \leq V_{CC} \leq 5.5 B$	500 200 100 50	ns

DC electrical characteristics

Symbol	Parameter	Test conditions	V _{CC} , V	Value						Unit
				25°C		-40°C to 85°C		-40°C to 125°C		
				min	max	min	max	min	max	
V _{IH}	High level input voltage	V _O = V _{CC} -0.1 V	1.2	0.9	-	0.9	-	0.9	-	V
			2.0	1.4	-	1.4	-	1.4	-	
			2.7	2.0	-	2.0	-	2.0	-	
			3.0	2.0	-	2.0	-	2.0	-	
			3.6	2.0	-	2.0	-	2.0	-	
			4.5	3.15	-	3.15	-	3.15	-	
			5.5	3.85	-	3.85	-	3.85	-	
V _{IL}	Low level input voltage	V _O = 0.1 B	1.2	-	0.3	-	0.3	-	0.3	V
			2.0	-	0.6	-	0.6	-	0.6	
			2.7	-	0.8	-	0.8	-	0.8	
			3.0	-	0.8	-	0.8	-	0.8	
			3.6	-	0.8	-	0.8	-	0.8	
			4.5	-	4.35	-	4.35	-	4.35	
			5.5	-	5.35	-	5.35	-	5.35	
V _{OH}	High level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 uA	1.2	1.05	-	1.0	-	1.0	-	V
			2.0	1.85	-	1.8	-	1.8	-	
			2.7	2.55	-	2.5	-	2.5	-	
			3.0	2.85	-	2.8	-	2.8	-	
			3.6	3.45	-	3.4	-	3.4	-	
			4.5	4.35	-	4.3	-	4.3	-	
V _{OL}	Low level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 uA	1.2	-	0.15	-	0.2	-	0.2	V
			2.0	-	0.15	-	0.2	-	0.2	
			2.7	-	0.15	-	0.2	-	0.2	
V _{OL}	Low level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 uA	3.0	-	0.15	-	0.2	-	0.2	V
			3.6	-	0.15	-	0.2	-	0.2	
			4.5	-	0.15	-	0.2	-	0.2	
			5.5	-	0.15	-	0.2	-	0.2	
			3.0	-	0.33	-	0.4	-	0.5	
V _{OL}	Low level output voltage	V _I = V _{IH} or V _{IL} ; I _O = 12 mA	4.5	-	0.40	-	0.55	-	0.65	V
			4.5	-	0.40	-	0.55	-	0.65	
I _I	Input current	V _I = V _{CC} or 0 V	5.5	-	±0.1	-	±1.0	-	±1.0	uA
I _{CC}	Consumption current	V _I = V _{CC} or 0 V I _O = 0 uA	5.5	-	8.0	-	80	-	160	uA
I _{CC1}	Additional input consumption current	V _I = V _{CC} -0.6 V; I _O = 0 uA	5.5	-	8.0	-	80	-	160	uA

AC electrical characteristics ($t_{LH} = t_{HL} = 2.5$ ns, $C_L=50$ pF, $R_L = 1$ KOhm)

Symbol	Parameter	Test conditions	V_{CC}, V	Value				-40 to 125 °C		Unit
				25 °C		-40 to 85 °C		min	max	
				min	max	min	max			
t_{PHL}, t_{PLH}	Propagation delay time when switching "on", "off"	Fig.1	1.2	-	80	-	85	-	95	ns
			2.0	-	17	-	21	-	26	
			2.7	-	12	-	15	-	19	
			3.0	-	10	-	12	-	15	
			4.5	-	8	-	10	-	13	
C_I	Input capacity	-	3.0	-	7	-	-	-	-	pF
C_{PD}	Dynamic capacity	$V_I = 0 V$ or V_{CC}	3.0	-	44	-	-	-	-	

- Time diagram of input and output pulses

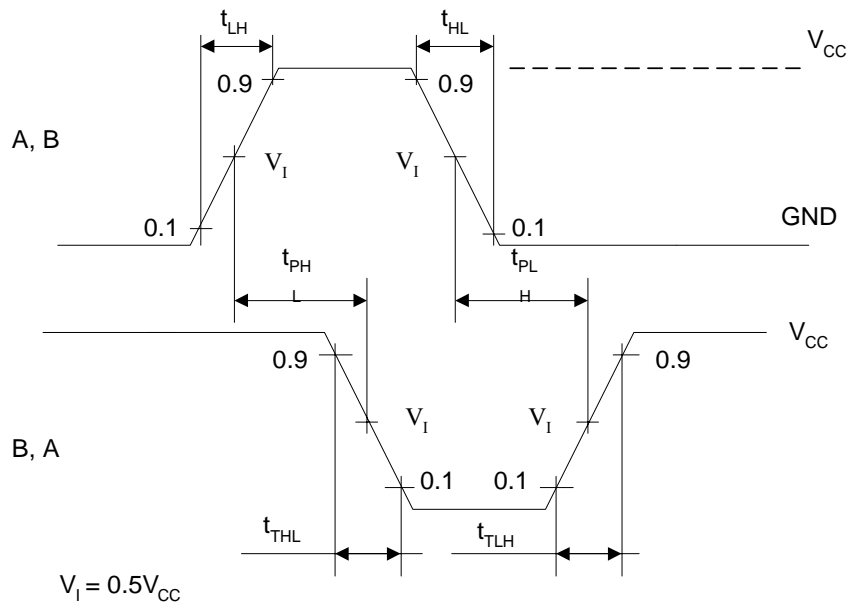
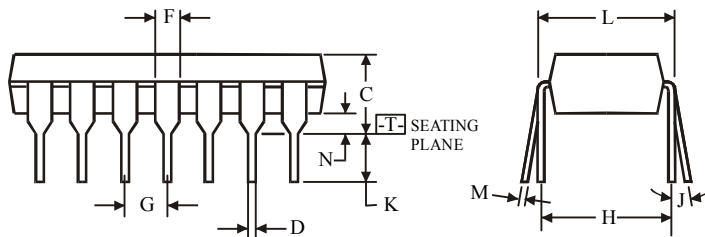
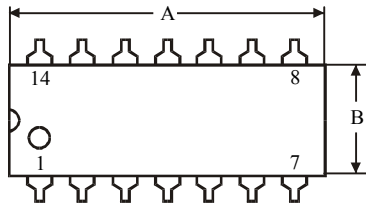
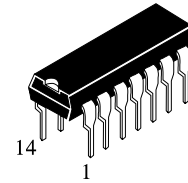


Fig.1

N SUFFIX PLASTIC DIP
(MS - 001AA)



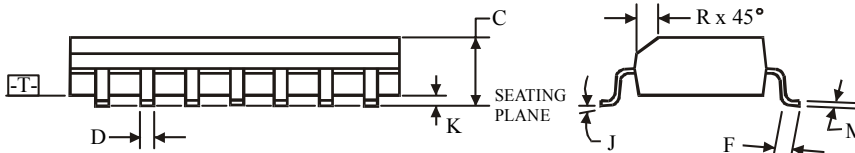
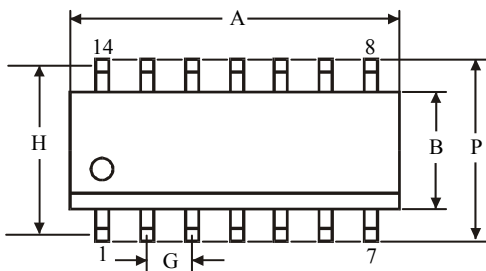
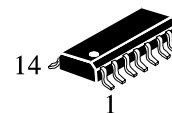
$\oplus 0.25 (0.010) \text{ (M) T}$

NOTES:

1. Dimensions "A", "B" do not include mold flash or protrusions.
Maximum mold flash or protrusions 0.25 mm (0.010) per side.

Symbol	Dimension, mm	
	MIN	MAX
A	18.67	19.69
B	6.1	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G	2.54	
H	7.62	
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.2	0.36
N	0.38	

D SUFFIX SOIC
(MS - 012AB)



$\oplus 0.25 (0.010) \text{ (M) T C (M)}$

NOTES:

1. Dimensions A and B do not include mold flash or protrusion.
2. Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B - 0.25 mm (0.010) per side.

Symbol	Dimension, mm	
	MIN	MAX
A	8.55	8.75
B	3.8	4
C	1.35	1.75
D	0.33	0.51
F	0.4	1.27
G	1.27	
H	5.27	
J	0°	8°
K	0.1	0.25
M	0.19	0.25
P	5.8	6.2
R	0.25	0.5